
APPLICATION DATA SHEET UNDER 37 C.F.R. §1.76

Inventor Information

Inventor One Given Name: **Didier**
Family Name: **Dutartre**
Postal Address: 1, Chemin du Gamond
City: Meylan
State or Province and Postal Code: 38240
Country: France
Citizenship: French

Inventor Two Given Name: **Patrick**
Family Name: **Jerier**
Postal Address: 10, Rue Auguste Ravier
City: Grenoble
State or Province and Postal Code: 38100
Country: France
Citizenship: French

Correspondence Information

Name Line One: **James H. Morris**
Name Line Two: Wolf, Greenfield & Sacks, P.C.
Address Line One: Federal Reserve Plaza
Address Line Two: 600 Atlantic Avenue
City: Boston
State or Province and Postal Code: Massachusetts 02210
Telephone: 617-720-3500
Fax: 617-720-2441
E-mail: jmorris@wolfgreenfield.com

Application Information

Title: METHOD OF EPITAXY ON A SILICON SUBSTRATE
COMPRISING AREAS HEAVILY DOPED WITH ARSENIC

Total Drawing Sheets: 4

Formal Drawings? Yes

Application Type: Non-Provisional Utility

Art Unit: Unknown

Docket Number: S1022/8562

Representative Information

Representative Customer Number:: 23628

Continuity Information

This application is a: Non-provisional

Claiming priority to: Non-Provisional application docket nos. S1022/8562 and S1022/8072

Serial Number: Not yet assigned

Filing Date: July 10, 2001

Status: Pending

Prior Foreign Applications

Foreign Application Number: 97/10032

Filing Date: July 31, 1997

Country: France

Priority Claimed: Yes

Assignee Information (when available)

Name of Assignee: STMicroelectronics S.A.

Address: 7, Avenue Gallieni, 94250 Gentilly, France